

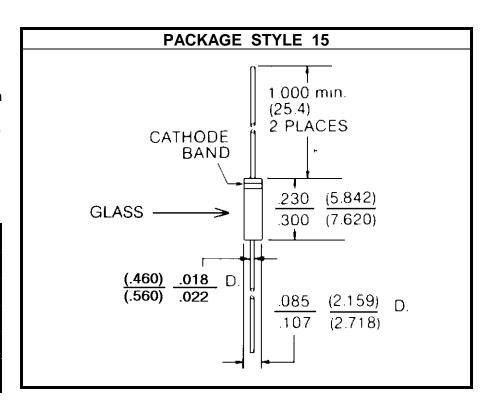
# SILICON ABRUPT JUNCTION TUNING VARACTOR

### **DESCRIPTION:**

The **ASI AT6021M** is an Epitaxial Silicon Abrupt Junction Microwave Tuning Varactor. This Device is Passivated With Silicon Dioxide Which Results in Very Low Leakage Current. The Capacitance Voltage Relationship Closely Approximates Square Law (n = 0.5).

### **MAXIMUM RATINGS**

Ic	100 mA				
$V_{CE}$	70 V				
P <sub>DISS</sub>	250 mW @ $T_C = 25$ $^{\circ}C$				
TJ	-65 to +150 °C				
T <sub>STG</sub>	-65 to +150 °C				
θ <sub>JC</sub>	0 <sub>JC</sub> 500 °C/W				



#### CHARACTERISTICS To = 25 °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
$V_{B}$	$I_R = 10 \mu A$		70			V
Ст	V <sub>R</sub> = 4.0 V	f = 1.0 MHz	44.65	47.0	49.35	pF
$\Delta C_{T}$	C <sub>T0</sub> /C <sub>T60</sub>	f = 1.0 MHz	7.4			
$\Delta C_{T}$	C <sub>T8</sub> /C <sub>T60</sub>	f = 1.0 MHz	2.50		2.60	
Q	V <sub>R</sub> = 4.0 V	f = 50 MHz	600			
T <sub>C</sub>	V <sub>R</sub> = 4.0 V				300	PPM/°C

## ADVANCED SEMICONDUCTOR, INC.